

N-channel 80 V, 27 mΩ standard level MOSFET in LFPAK33 19 September 2016 Product data sheet

1. General description

Standard level N-channel MOSFET in an LFPAK33 (Power33) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

2. Features and benefits

- Q101 Compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with V_{GS(th)} rating of greater than 1 V at 175 °C

3. Applications

- 12 V, 24 V and 48 V automotive systems
- Motors, lamps and solenoid control
- Transmission control
- Ultra high performance power switching

4. Quick reference data

Table 1. Quie	ck reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C	-	-	80	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>	-	-	30	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>	-	-	62	W
Static characte	eristics					
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 5 A; T _j = 25 °C; <u>Fig. 11</u>	-	22	27	mΩ
Dynamic chara	acteristics					
Q _{GD}	gate-drain charge	$I_D = 5 \text{ A}; V_{DS} = 64 \text{ V}; V_{GS} = 10 \text{ V};$ $T_j = 25 \text{ °C}; \text{ Fig. 13}; \text{ Fig. 14}$	-	6.2	-	nC

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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	Source		D
2	S	Source		
3	S	Source	\bigcirc	G
4	G	Gate		mbb076 S
mb	D	Mounting base; connected to drain	LFPAK33 (SOT1210)	

6. Ordering information

Table 3. Ordering information						
Type number	Package	3				
	Name	Description	Version			
BUK7M27-80E	LFPAK33	Plastic single ended surface mounted package (LFPAK33); 8 leads	SOT1210			

7. Marking

Table 4. Marking codes	
Type number	Marking code
BUK7M27-80E	72780E

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Мах	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C	-	80	V
V _{DGR}	drain-gate voltage	R _{GS} = 20 kΩ	-	80	V
V _{GS}	gate-source voltage	DC; T _j ≤ 175 °C	-20	20	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>	-	62	W
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>	-	30	А
		V _{GS} = 10 V; T _{mb} = 100 °C; <u>Fig. 2</u>	-	21.3	А
I _{DM}	peak drain current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^\circ C$; Fig. 3	-	121	А
T _{stg}	storage temperature		-55	175	°C

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Symbol	Parameter	Conditions		Min	Мах	Unit
Tj	junction temperature			-55	175	°C
Source-drai	in diode		1			
I _S	source current	T _{mb} = 25 °C		-	30	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^\circ C$		-	121	А
Avalanche	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\label{eq:ID} \begin{split} I_D &= 30 \; \text{A}; \; V_{sup} \leq 80 \; \text{V}; \; \text{R}_{GS} = 50 \; \Omega; \\ V_{GS} &= 10 \; \text{V}; \; \text{T}_{j(\text{init})} = 25 \; ^{\circ}\text{C}; \; \text{unclamped}; \\ \hline \text{Fig. 4} \end{split}$	[1][2]	-	28.3	mJ

[1] Single-pulse avalanche rating limited by maximum junction temperature of 175 $^\circ$ C.

[2] Refer to application note AN10273 for further information.

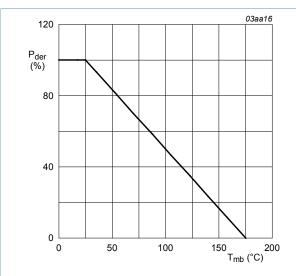
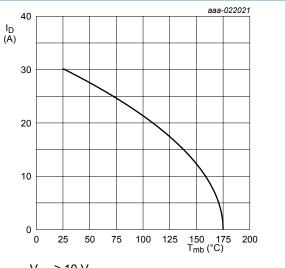


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

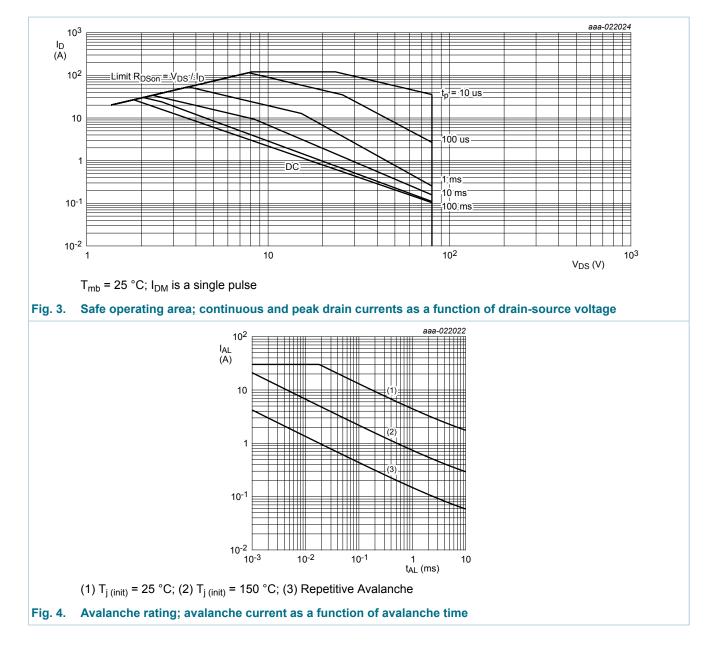


V_{GS} ≥ 10 V

Fig. 2. Continuous drain current as a function of mounting base temperature

$$I_D = 30A \times \sqrt{\frac{175^{\circ}C - T_{mb}}{150^{\circ}C}}$$
 for $T_{mb} \ge 25^{\circ}C$

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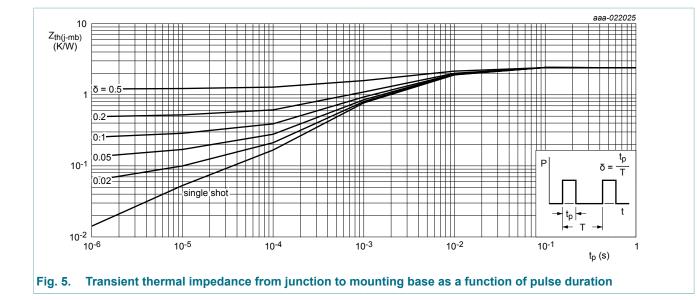


9. Thermal characteristics

Table 6. The	rmal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	<u>Fig. 5</u>	_	2.01	2.43	K/W

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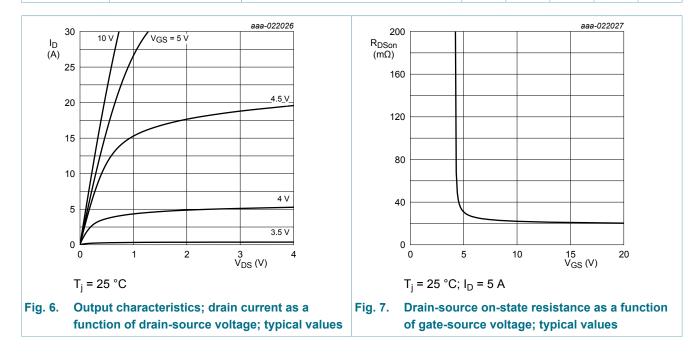
10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS} drain-source breakdown voltage		I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	80	-	-	V
	breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = -55 °C	72	-	-	V
V _{GS(th)} gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 25 °C; Fig. 9; Fig. 10	2.4	3	4	V	
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 9	-	-	4.5	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 9	1	-	-	V
I _{DSS}	s drain leakage current	V_{DS} = 80 V; V_{GS} = 0 V; T_j = 25 °C	-	0.01	1	μA
		V _{DS} = 80 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μA
I _{GSS}	gate leakage current	V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state	V _{GS} = 10 V; I _D = 5 A; T _j = 25 °C; <u>Fig. 11</u>	-	22	27	mΩ
	resistance	V _{GS} = 10 V; I _D = 5 A; T _j = 175 °C; Fig. 12	-	-	68	mΩ
Dynamic ch	naracteristics	· ·				
Q _{G(tot)}	total gate charge	I _D = 5 A; V _{DS} = 64 V; V _{GS} = 10 V;	-	19.5	-	nC
Q _{GS}	gate-source charge $T_j = 25 \text{ °C}; \text{ Fig. 13}; \text{ Fig. 14}$ gate-drain charge	T _j = 25 °C; <u>Fig. 13; Fig. 14</u>	-	4.1	-	nC
Q _{GD}		-	6.2	-	nC	

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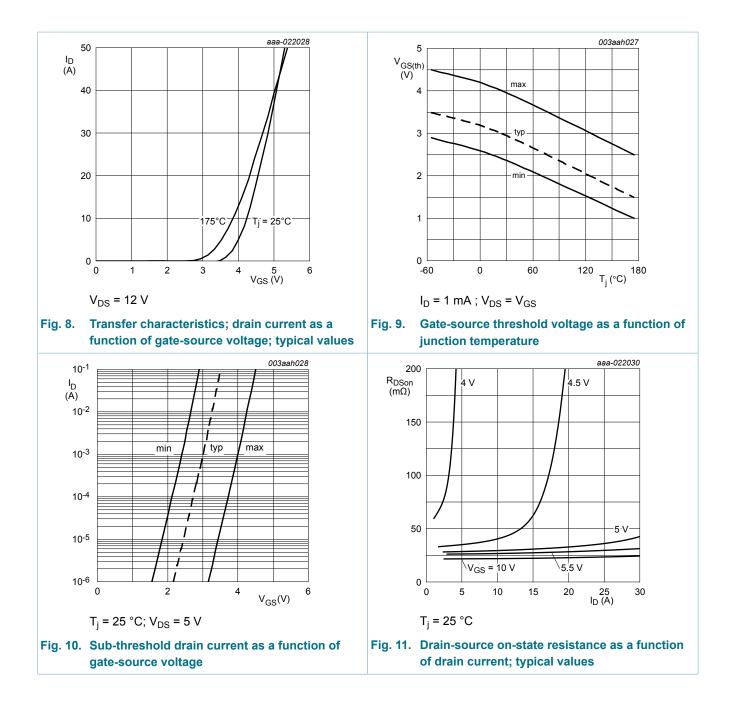
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Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
C _{iss}	input capacitance	V_{DS} = 25 V; V_{GS} = 0 V; f = 1 MHz;	-	982	1306	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 15</u>	-	109	130	pF
C _{rss}	reverse transfer capacitance		-	65	89	pF
t _{d(on)}	turn-on delay time	V_{DS} = 60 V; R _L = 2 Ω; V _{GS} = 10 V;	-	5.6	-	ns
t _r	rise time	R _{G(ext)} = 5 Ω; T _j = 25 °C	-	8.6	-	ns
t _{d(off)}	turn-off delay time		-	13.5	-	ns
t _f	fall time		-	8.7	-	ns
Source-dra	in diode	1	1			
V _{SD}	source-drain voltage	$I_{S} = 5 \text{ A}; V_{GS} = 0 \text{ V}; T_{j} = 25 \text{ °C}; Fig. 16$	-	0.8	1.2	V
t _{rr}	reverse recovery time	I_{S} = 5 A; dI _S /dt = -100 A/µs; V _{GS} = 0 V;	-	21.6	-	ns
Q _r	recovered charge	V _{DS} = 25 V; T _j = 25 °C	-	24.2	-	nC



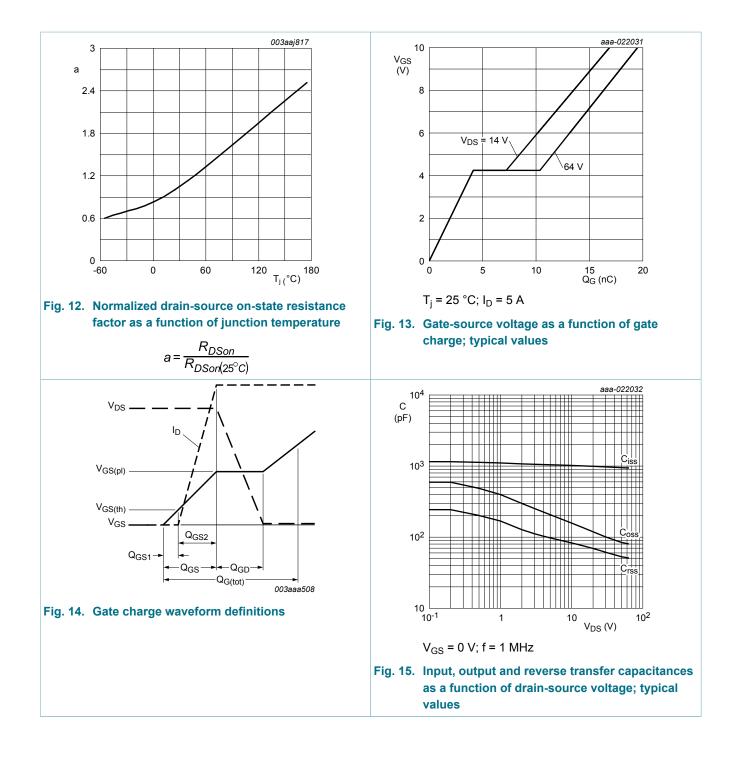
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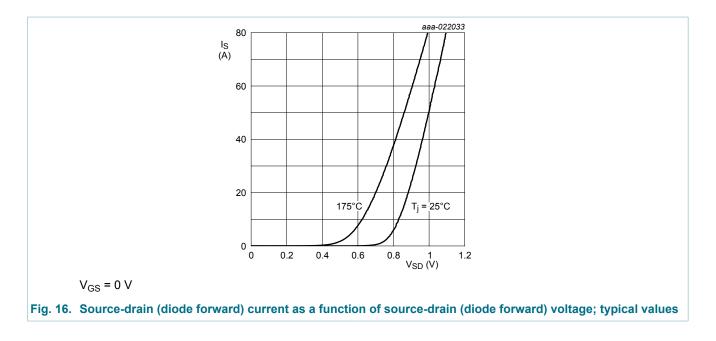
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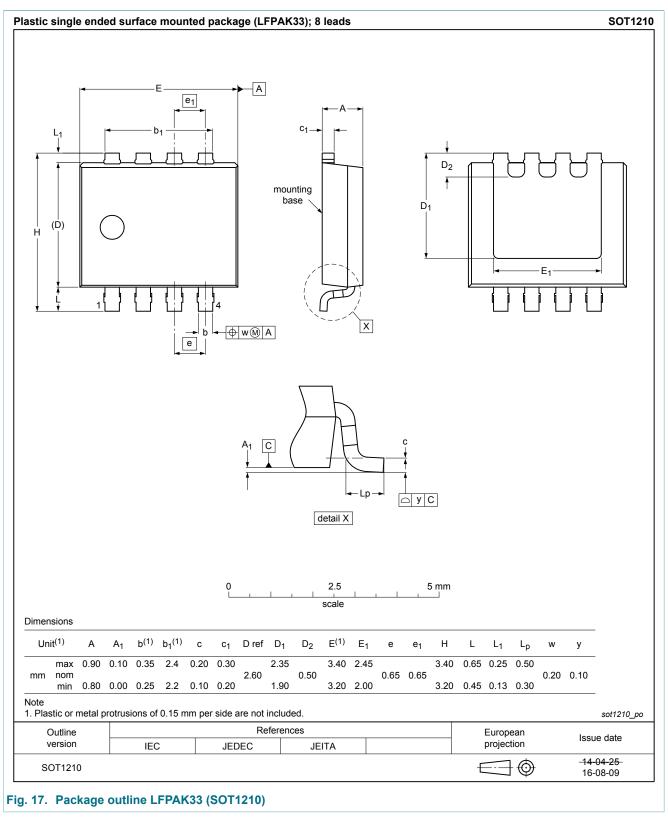


11. Application information

For guidance on how to use and understand this datasheet, please refer to application note <u>AN11158</u> "Understanding power MOSFET datasheet parameters".

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12. Package outline



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13. Legal information

13.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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